

Quarterly Reliability Monitoring Results

Quarters: Q1/2021 to Q4/2021

Based on structural similarity

Supplier Nexperia B.V. Name of Laboratory Assembly reliability labs Based on AEC-Q101 Test		User Part Number						
		BCP51-16T Part Description						
								Nexperia DHAM Small Signal Bipolar Transistor
		SMD package						
		Test Conditions	Duration	# Lots	# Quantity	# Rejects		
			TEST					
# E1	Pre- and Post-Stress Electrical Test	Tamb = 25 °C	NI/A	aaa bala	all name	ann balaur		
# []	Liectrical rest		N/A	see below	all parts	see below		
		JESD22-A113 Bake Tamb = 125 °C	24 hours					
	PC	Soak Tamb = 125 °C, RH = 85%	168 hours					
# A1	Preconditioning	Reflow soldering	3 cycles	849	61170	0		
		MIL-STD-750-1						
	HTRB	M1039 Method A						
		Tj = Tjmax, Vr = 100% of max. datasheet						
# B1	Bias	reverse voltage	1000 hours	202	16160	0		
	тс	JESD22-A104						
# A4	Temperature Cycling	-65 °C to Tjmax, not to exceed 150°C	1000 cycles	171	13680	0		
,,,,,,	· · · · · · · · · · · · · · · · · · ·	JESD22-A102						
	AC	Tamb = 121 °C, RH = 100 %						
# A3 alt	Autoclave	Pressure = 205 kPa (29.7 psia)	96 hours	173	13840	0		
	H3TRB	JESD22-A101						
" A D II	High Humidity High Temperature Reverse Bias	Tamb = 85 °C, RH = 85%, VR = 80 % of	10001	470	10010	•		
# A2 alt	Temperature Reverse Bias		1000 hours	173	13840	0		
	IOL	MIL-STD-750 Method 1037 ton = toff, devices powered to insure ΔT_j =						
# A5	Intermittent Operating Life		1000 hours	197	15760	0		
# A3		,	2000 1100/3	-51	25700	<u> </u>		
	RSH	JESD22-A111						
# C8	Resistance to Solder Heat	260 °C ± 5 °C	10 s	135	4050	0		
	SD							
# C10	Solderability	J-STD-002		342	3420	0		

^[1] The maximum applied voltage is limited by test chamber set up and does not exceed 115V.

Calculation of FIT and MTTF

Test considered for FIT calculation: High Temperature Reverse Bias (HTRB, Test #B1)
Confidence level 60%, derated to 55 °C, activation energy 0.7 eV, test time 168 to 1000 hours

Wafer Fab	Technology	Quantity	Rejects	Failure Rate (FIT)	MTTF (hrs)
Nexperia	Small Signal Bipolar				
DHAM	Transistor	16160	0	0.26	3.81E+09

© 2022 Nexperia B.V.

All information hereunder is per Nexperia's best knowledge. This document does not provide for any representation or warranty express or implied by Nexperia. In case Nexperia has tested the product, this documentation reflects the outcome of the analysis of the actually tested parts only.

nexperia.com